BEST AVAILABLE COPY

Chamber A pressure s	ethoint deviati	on warning.			more	,	
Dystem Wafer Ch A Ch		Ch F	Xfer LL f	i LL B <u>Progra</u>		A LL B Pro	ogram His
4_5t	eps for Epi	Process Recipe	H2 BAKE				ele ≢∰
	SAC ANEAL						•
•	+-Step <u>i</u>	+-Step <u>2</u>		-Step <u>3</u>		-Step 4	
	i <u>PURGE</u>	i HEAT UP		BAKE		COOL DOWN	
Chamber Selection	i A11	i A1	1 1	A11		Al	1
Glep End Control	i By Time	By Time	i	By Time	. i	By Time	
Maximum Step Time 🤺					onds i	. 30	Seconds
Temp Hode : Target	iConst Pwr: 20.	00 kWiLower PID:	1000.0 CIL	ower PID: 10	00.0 C:10	Const Pwr:	2.00 k
Tamp Nate : PIDs							Default
iwwi: U In A: L In X	1 50 A: 40 A:	40 %1 51 %: 44	×: 44 ×1	5i %: 44 %:	44 %.1	50 x: 40	≯: 40
Pomer / Ramp	i Constant Pwr	メ i Constant	Pwr 😕 🚺	Constant Pw	r× i	Constant	Pwr X
Fressure H <mark>ode</mark>	iServo to Press	ure iControl as	Before id	Control as Be	fore is	iervo to P	ressure
Pian yman . isg n		0 T/5i .	i		i	80.00 T	20.00 T/
Sas Rames and Flows	`i:	i:	i_	 :	i_	:	
	;:	i:	i_	<u> </u>	i	:	
	i:	i:	i_	:	i _		
	i;	i:	i_	•	i_	:	
	i:	i:	i_		i_	:	
Frac/Elch Gas Dest.	iProc:Vent Etch	:VentiProc:Vent	Etch:VentIP	roc:Vent Etc	h:Vent JĒ	rocivent	Etch:Ven
Main & Slit Purges	19:30.00 S: 5.0	0w/H2IM:30.00 5:	5.00w/H2HH	1:20.00 S: 4.	00w/H2 _j jir	:35.00 S:	10.00w/H
	i <u>Charting con</u>	<u>trol</u> i <u>Charting</u>	<u>control</u>	Charting co	ntrol 1	Charting	control
_	i <u>Expand Step</u>	<u>Expand</u>	Step i	Expand Ste	p i	Expand 9	St p
Step Status/Command	i Valid Step /	Copy Valid Ste	p / Copy i	Valid Step /	Copy 1	Valid St	р / Сору
<u>Directory</u> Header		<u>Delete Add Be</u>	<u>fore</u> Add	After 5t	eps > idd	After	• •
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